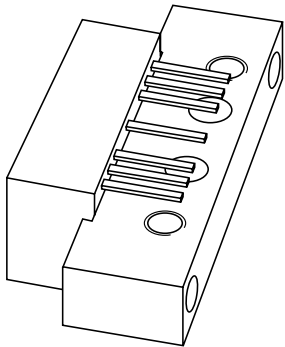


# DATA SHEET



## **CGD914; CGD914MI** 860 MHz, 20 dB gain power doubler amplifier

Product specification  
Supersedes data of 2000 Jul 25

2001 Nov 01

860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI

FEATURES

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

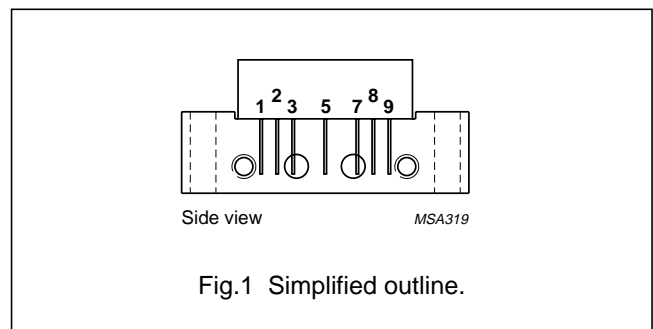
- CATV systems operating in the 40 to 870 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating at a voltage supply of 24 V (DC), employing both GaAs and Si dies. Both modules are electrically identical, only the pinning is different.

PINNING - SOT115J

PIN	DESCRIPTION	
	CGD914	CGD914MI
1	input	output
2 and 3	common	common
5	+V <sub>B</sub>	+V <sub>B</sub>
7 and 8	common	common
9	output	input



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 45 MHz	19.75	20.25	dB
		f = 870 MHz	20.2	21.5	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	345	375	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V <sub>B</sub>	supply voltage	–	30	V
V <sub>i</sub>	RF input voltage	–	–	
	single tone	–	70	dBmV
	132 channels flat	–	45	dBmV
T <sub>stg</sub>	storage temperature	–40	+100	°C
T <sub>mb</sub>	operating mounting base temperature	–20	+100	°C

## 860 MHz, 20 dB gain power doubler amplifier

## CGD914; CGD914MI

**CHARACTERISTICS**Bandwidth 45 to 870 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75$   $\Omega$ .

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 45 MHz	19.75	20	20.25	dB
		f = 870 MHz	20.2	21	21.5	dB
SL	slope straight line	f = 45 to 870 MHz	0.2	1	1.5	dB
FL	flatness straight line	f = 45 to 100 MHz	-0.25	-	+0.25	dB
		f = 100 to 800 MHz	-0.6	-	+0.4	dB
		f = 800 to 870 MHz	-0.45	-	+0.2	dB
	flatness narrow band	in each 6 MHz segment	-	-	±0.1	dB
S <sub>11</sub>	input return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	20	-	-	dB
		f = 160 to 320 MHz	18	-	-	dB
		f = 320 to 550 MHz	16	-	-	dB
		f = 550 to 650 MHz	15	-	-	dB
		f = 650 to 750 MHz	14	-	-	dB
		f = 750 to 870 MHz	14	-	-	dB
		f = 870 to 914 MHz	10	-	-	dB
S <sub>22</sub>	output return losses	f = 40 to 80 MHz	21	-	-	dB
		f = 80 to 160 MHz	21	-	-	dB
		f = 160 to 320 MHz	20	-	-	dB
		f = 320 to 550 MHz	19	-	-	dB
		f = 550 to 650 MHz	18	-	-	dB
		f = 650 to 750 MHz	17	-	-	dB
		f = 750 to 870 MHz	16	-	-	dB
		f = 870 to 914 MHz	14	-	-	dB
S <sub>21</sub>	phase response	f = 50 MHz	-45	-	+45	deg
S <sub>12</sub>	reverse isolation	RF <sub>out</sub> to RF <sub>in</sub>	-	-	22	dB
CTB	composite triple beat	79 chs; f <sub>m</sub> = 445.25 MHz; note 1	-	-	-76	dB
		112 chs; f <sub>m</sub> = 649.25 MHz; note 2	-	-	-64	dB
		132 chs; f <sub>m</sub> = 745.25 MHz; note 3	-	-	-55	dB
		79 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 547.25 MHz	-	-	-73	dB
		112 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 745.25 MHz	-	-	-64	dB
		132 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 745.25 MHz	-	-	-60	dB
X <sub>mod</sub>	cross modulation	79 chs; f <sub>m</sub> = 55.25 MHz; note 1	-	-	-70	dB
		112 chs; f <sub>m</sub> = 55.25 MHz; note 2	-	-	-62	dB
		132 chs; f <sub>m</sub> = 55.25 MHz; note 3	-	-	-57	dB
		79 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 55.25 MHz	-	-	-69	dB
		112 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 55.25 MHz	-	-	-65	dB
		132 chs flat; V <sub>o</sub> = 44 dBmV; f <sub>m</sub> = 55.25 MHz	-	-	-63	dB

## 860 MHz, 20 dB gain power doubler amplifier

## CGD914; CGD914MI

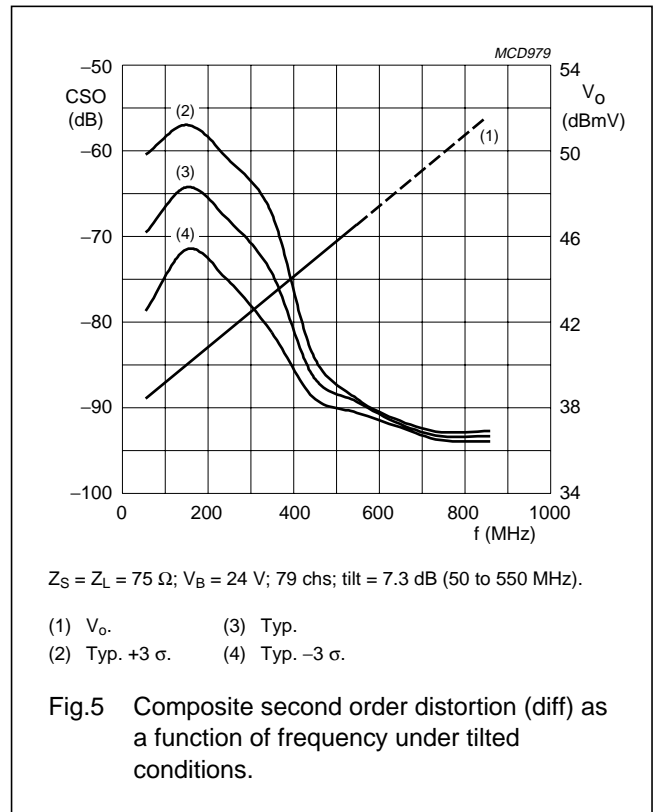
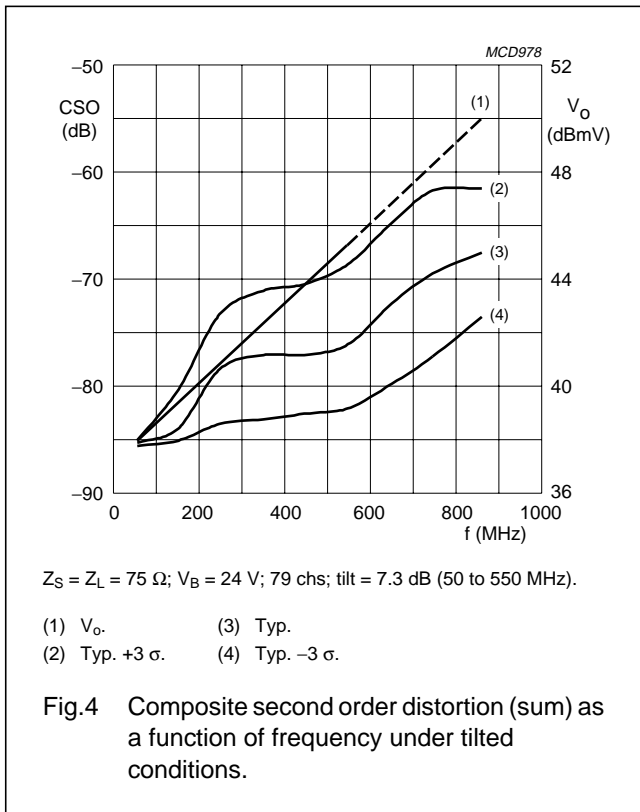
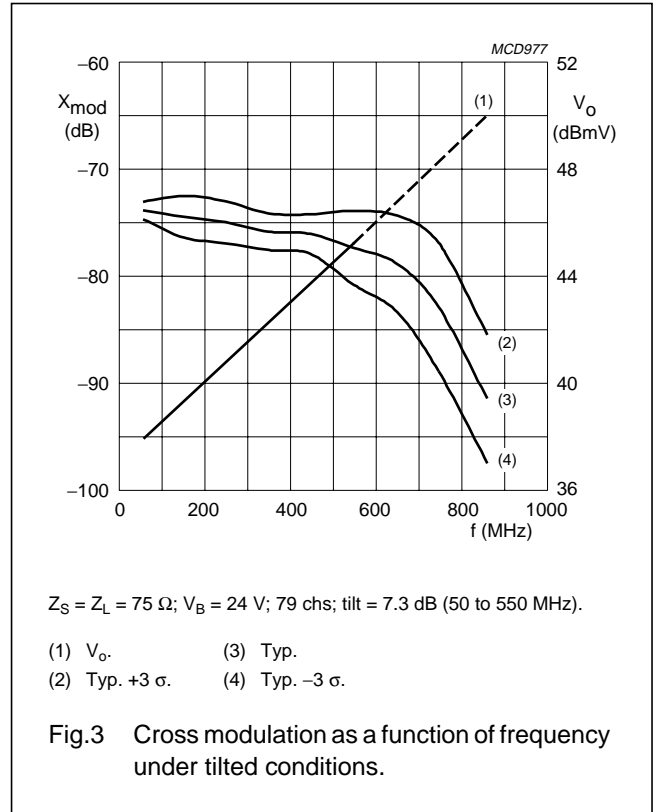
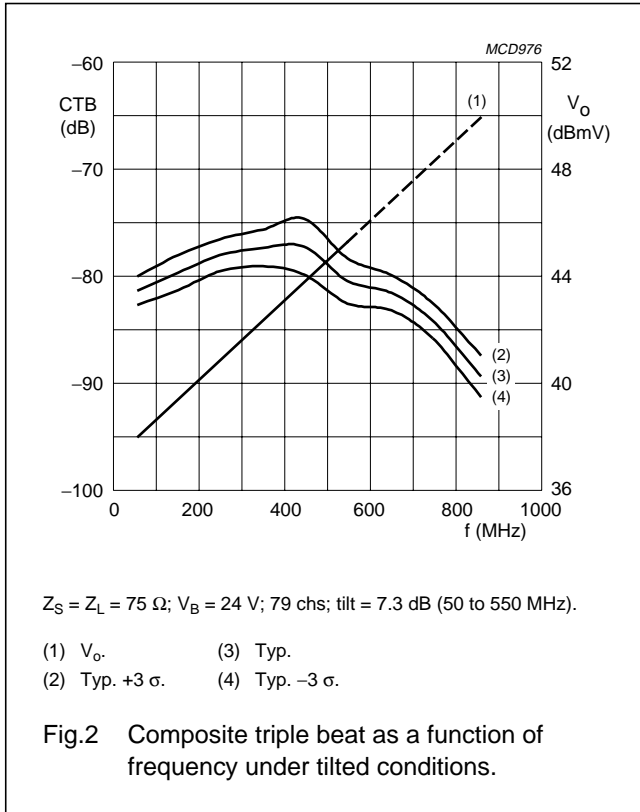
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CSO Sum	composite second order distortion (sum)	79 chs; $f_m = 446.5$ MHz; note 1	–	–	–71	dB
		112 chs; $f_m = 746.5$ MHz; note 2	–	–	–60	dB
		132 chs; $f_m = 860.5$ MHz; note 3	–	–	–56	dB
		79 chs flat; $V_o = 44$ dBmV; $f_m = 548.5$ MHz	–	–	–63	dB
		112 chs flat; $V_o = 44$ dBmV; $f_m = 746.5$ MHz	–	–	–54	dB
		132 chs flat; $V_o = 44$ dBmV; $f_m = 860.5$ MHz	–	–	–49	dB
CSO Diff	composite second order distortion (diff)	79 chs; $f_m = 150$ MHz; note 1	–	–	–59	dB
		112 chs; $f_m = 150$ MHz; note 2	–	–	–53	dB
		132 chs; $f_m = 150$ MHz; note 3	–	–	–48	dB
		79 chs flat; $V_o = 44$ dBmV; $f_m = 150$ MHz	–	–	–60	dB
		112 chs flat; $V_o = 44$ dBmV; $f_m = 150$ MHz	–	–	–59	dB
		132 chs flat; $V_o = 44$ dBmV; $f_m = 150$ MHz	–	–	–57	dB
NF	noise figure	$f = 50$ MHz	–	2.5	3	dB
		$f = 550$ MHz	–	2.5	3	dB
		$f = 750$ MHz	–	2.6	3.5	dB
		$f = 870$ MHz	–	3	3.5	dB
$d_2$	second order distortion	note 4	–	–	–60	dB
		note 5	–	–	–54	dB
		note 6	–	–	–50	dB
$V_o$	output voltage	$d_{im} = -60$ dB; note 7	69	–	–	dBmV
		$d_{im} = -60$ dB; note 8	66	–	–	dBmV
		$d_{im} = -60$ dB; note 9	63	–	–	dBmV
$I_{tot}$	total current consumption (DC)	note 10	345	360	375	mA

**Notes**

- $V_o = 38$  dBmV at 54 MHz; Tilt = 7.3 dB (55 to 547 MHz) extrapolated to 12 dB at 870 MHz.
- $V_o = 38$  dBmV at 54 MHz; Tilt = 10.2 dB (55 to 745 MHz) extrapolated to 12 dB at 870 MHz.
- $V_o = 38$  dBmV at 54 MHz; Tilt = 12 dB (55 to 865 MHz).
- $f_p = 55.25$  MHz;  $V_p = 60$  dBmV;  $f_q = 493.25$  MHz;  $V_q = 60$  dBmV; measured at  $f_p + f_q = 548.5$  MHz.
- $f_p = 55.25$  MHz;  $V_p = 60$  dBmV;  $f_q = 691.25$  MHz;  $V_q = 60$  dBmV; measured at  $f_p + f_q = 746.5$  MHz.
- $f_p = 55.25$  MHz;  $V_p = 60$  dBmV;  $f_q = 805.25$  MHz;  $V_q = 60$  dBmV; measured at  $f_p + f_q = 860.5$  MHz.
- Measured according to DIN45004B:  $f_p = 540.25$  MHz;  $V_p = V_o$ ;  $f_q = 547.25$  MHz;  $V_q = V_o - 6$  dB;  $f_r = 549.25$  MHz;  $V_r = V_o - 6$  dB; measured at  $f_p + f_q - f_r = 538.25$  MHz.
- Measured according to DIN45004B:  $f_p = 740.25$  MHz;  $V_p = V_o$ ;  $f_q = 747.25$  MHz;  $V_q = V_o - 6$  dB;  $f_r = 749.25$  MHz;  $V_r = V_o - 6$  dB; measured at  $f_p + f_q - f_r = 738.25$  MHz.
- Measured according to DIN45004B:  $f_p = 851.25$  MHz;  $V_p = V_o$ ;  $f_q = 858.25$  MHz;  $V_q = V_o - 6$  dB;  $f_r = 860.25$  MHz;  $V_r = V_o - 6$  dB; measured at  $f_p + f_q - f_r = 849.25$  MHz.
- The module normally operates at  $V_B = 24$  V, but is able to withstand supply transients up to 30 V.

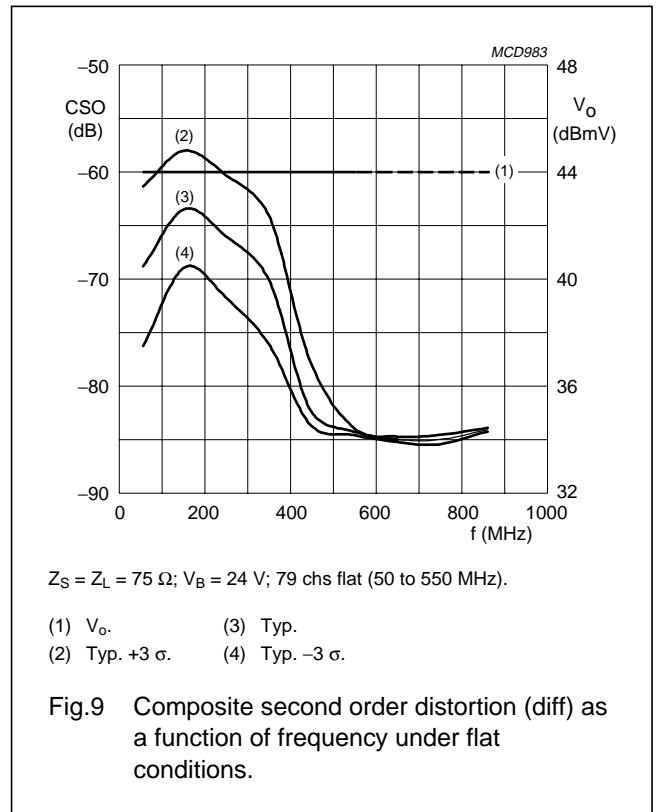
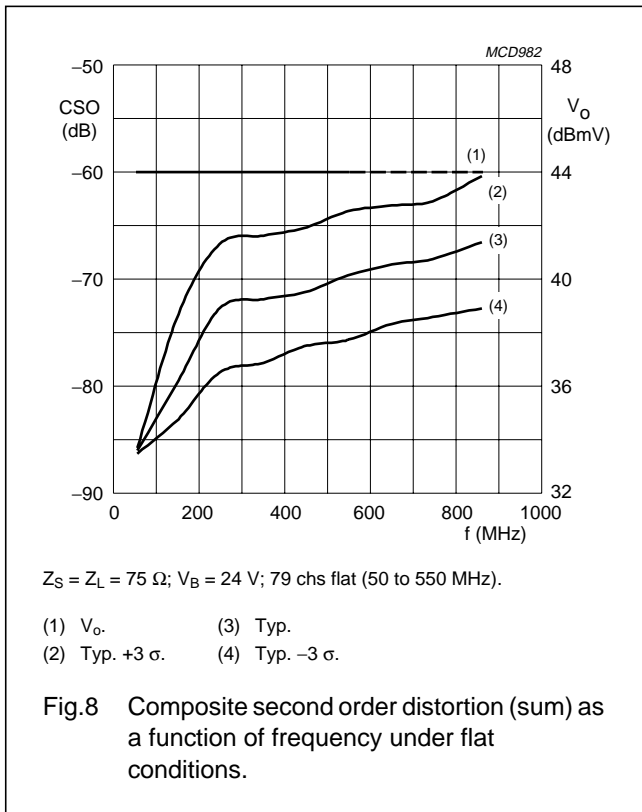
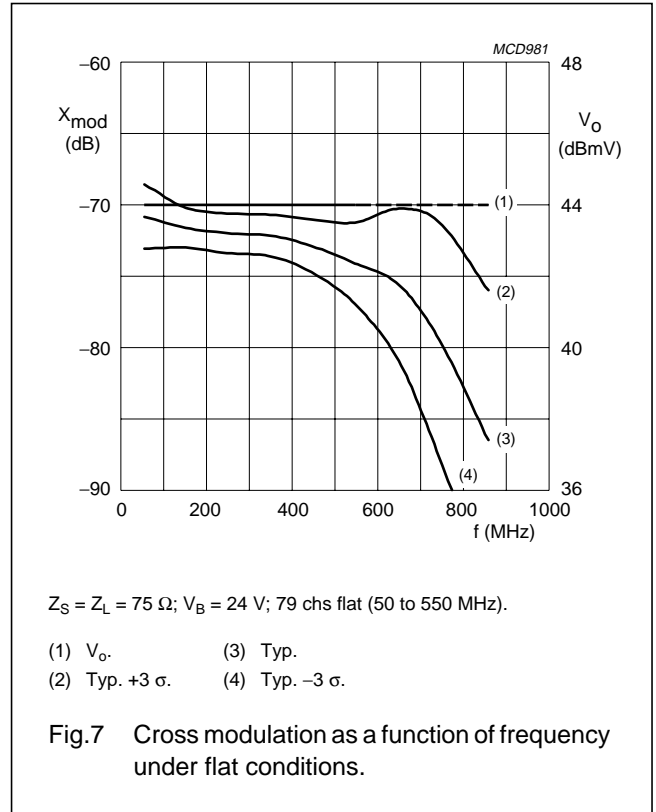
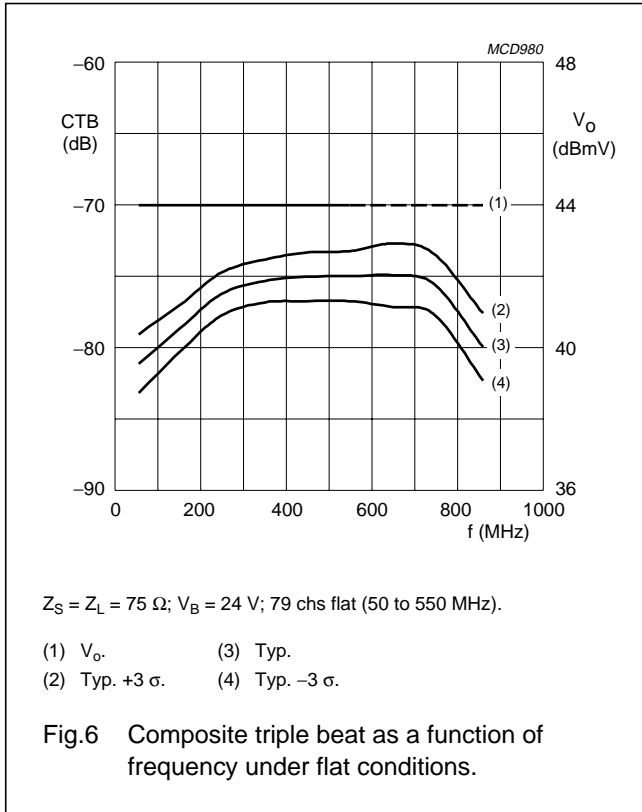
860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI



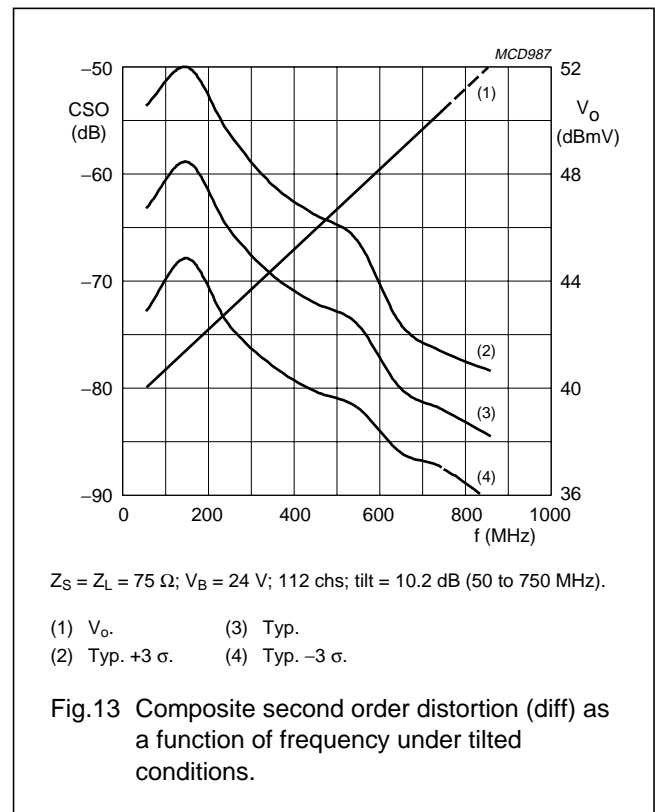
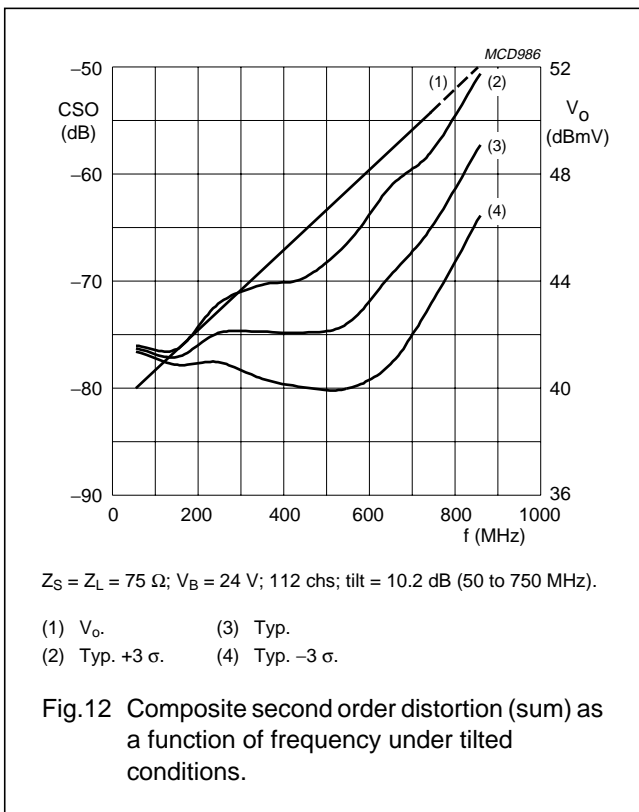
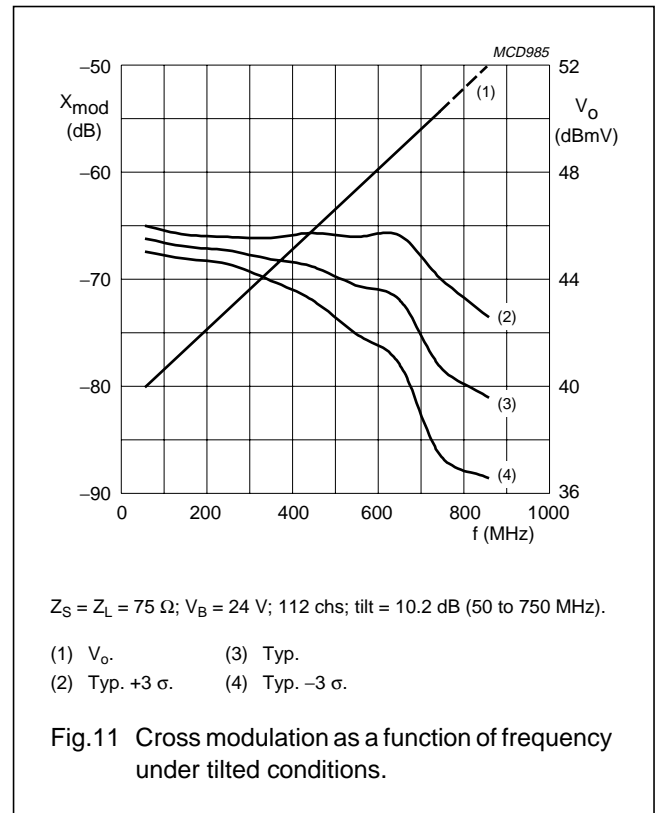
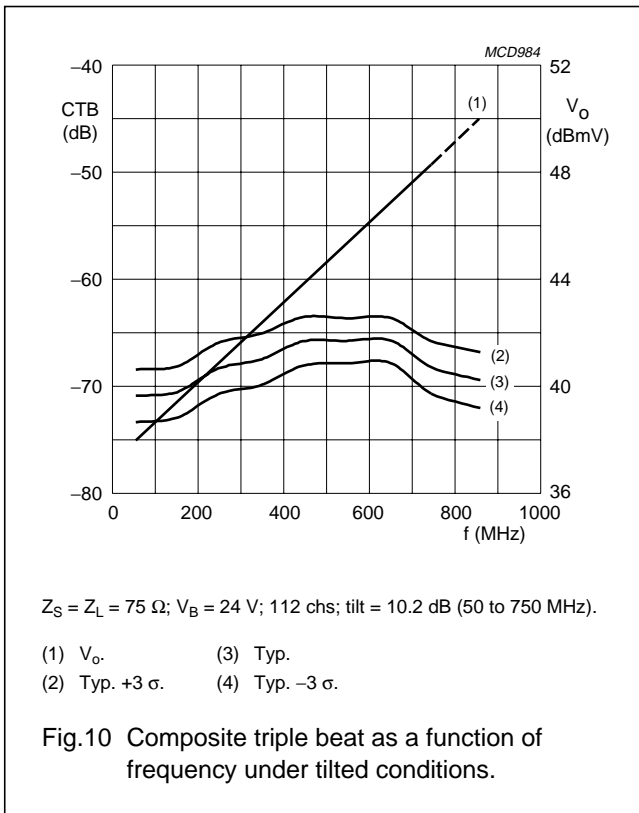
860 MHz, 20 dB gain power doubler amplifier

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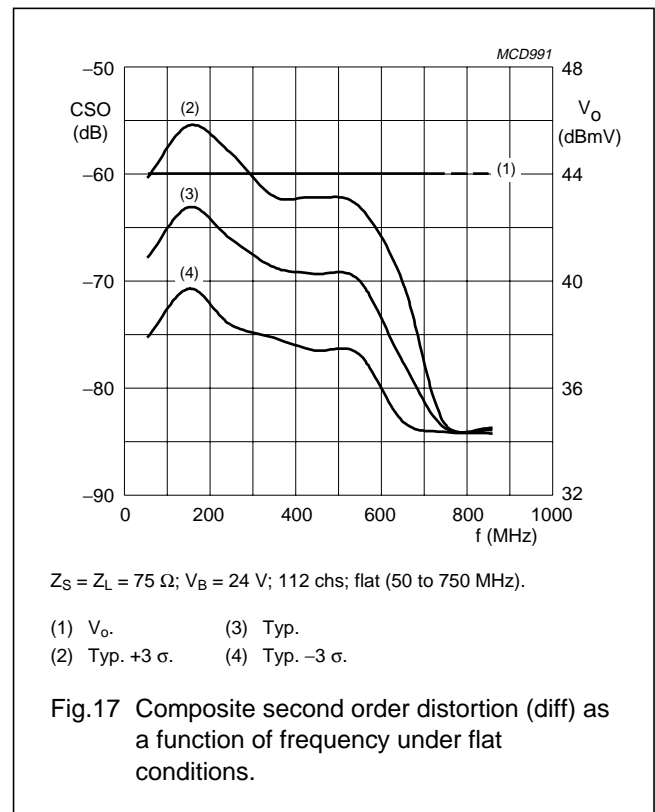
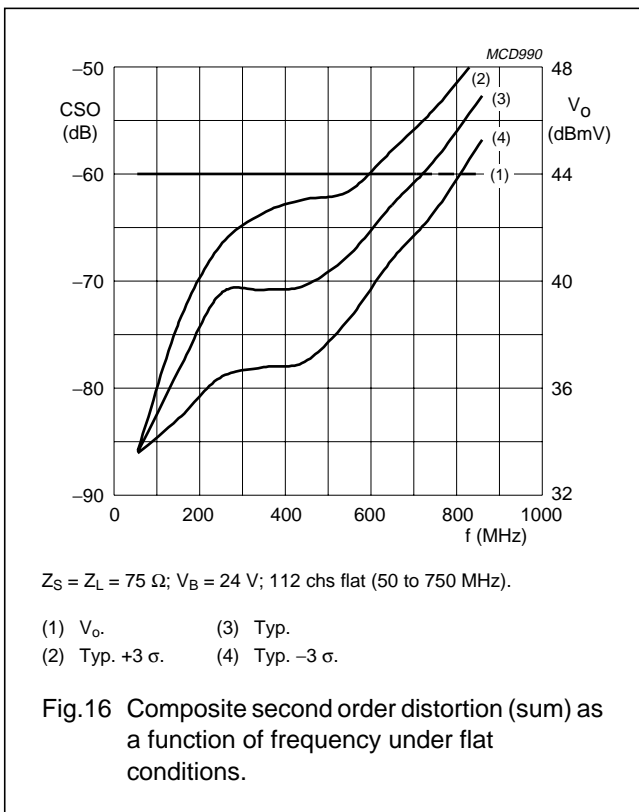
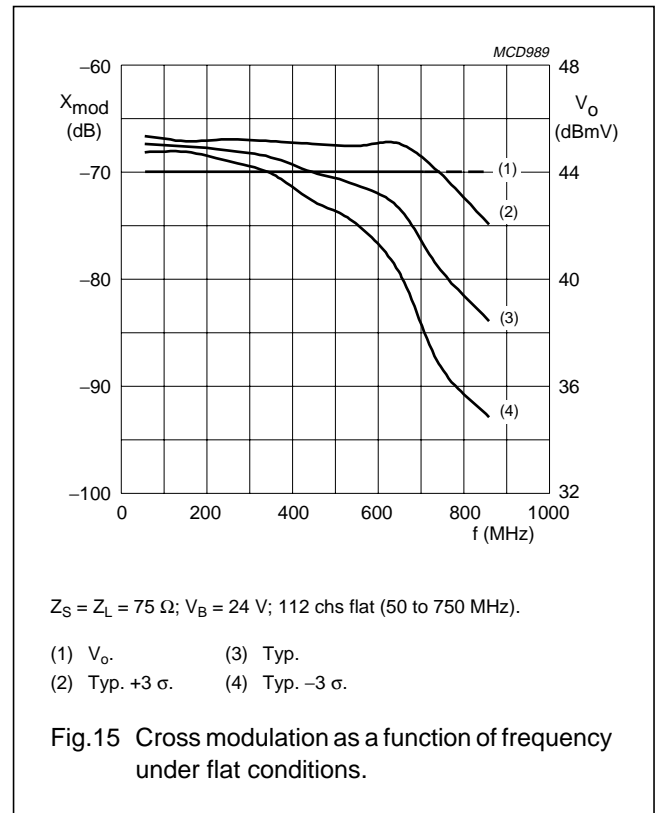
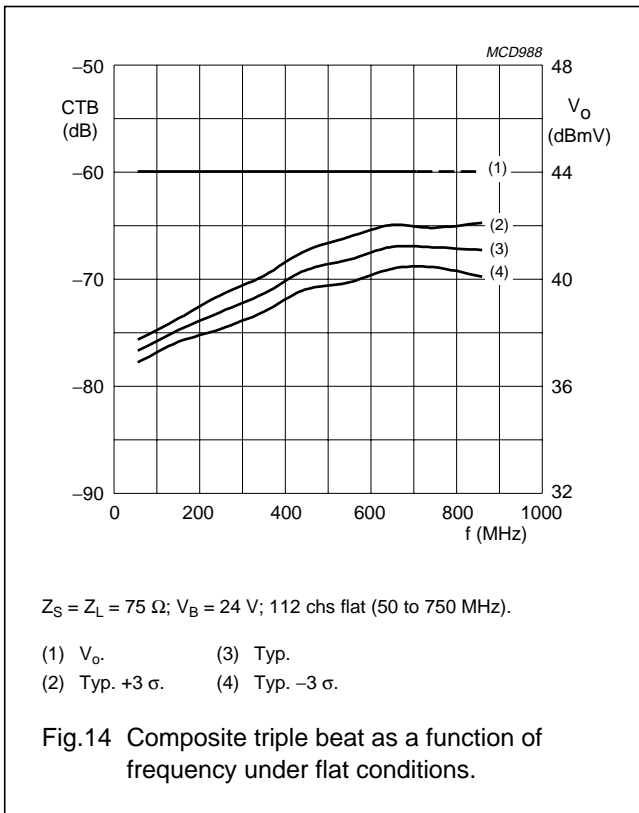
860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI



860 MHz, 20 dB gain power doubler amplifier

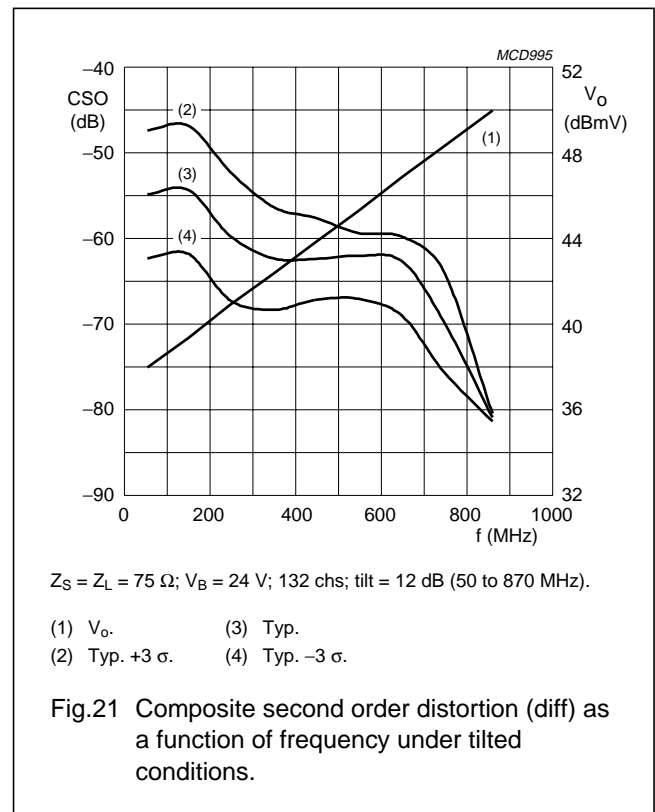
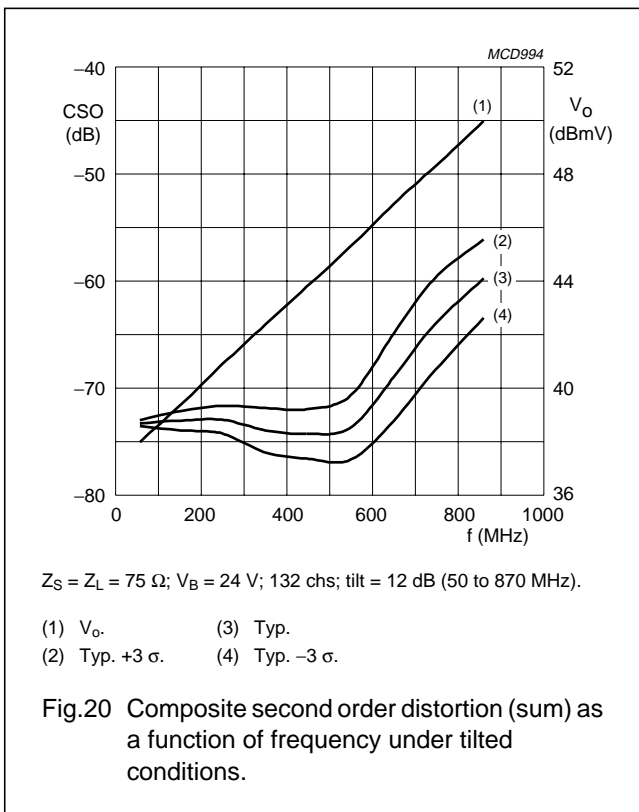
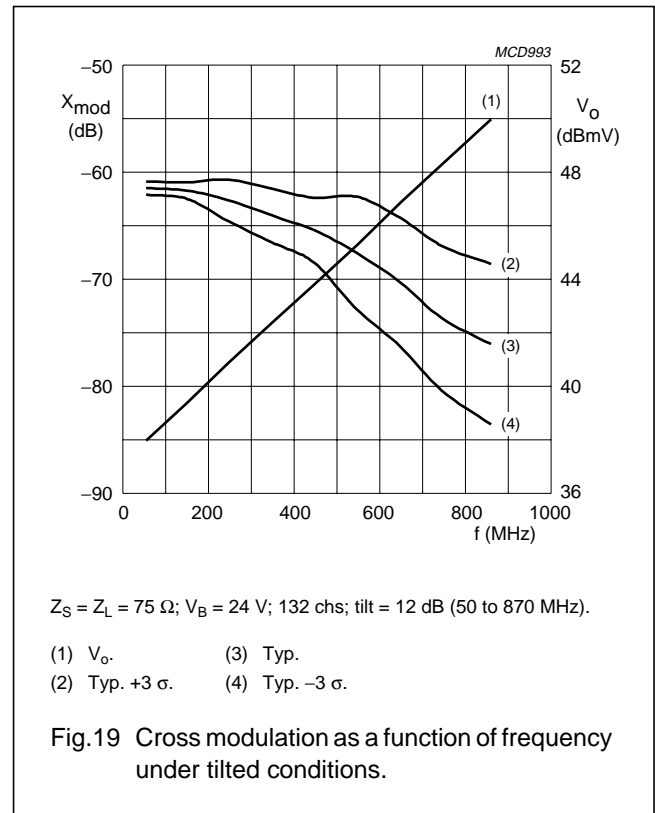
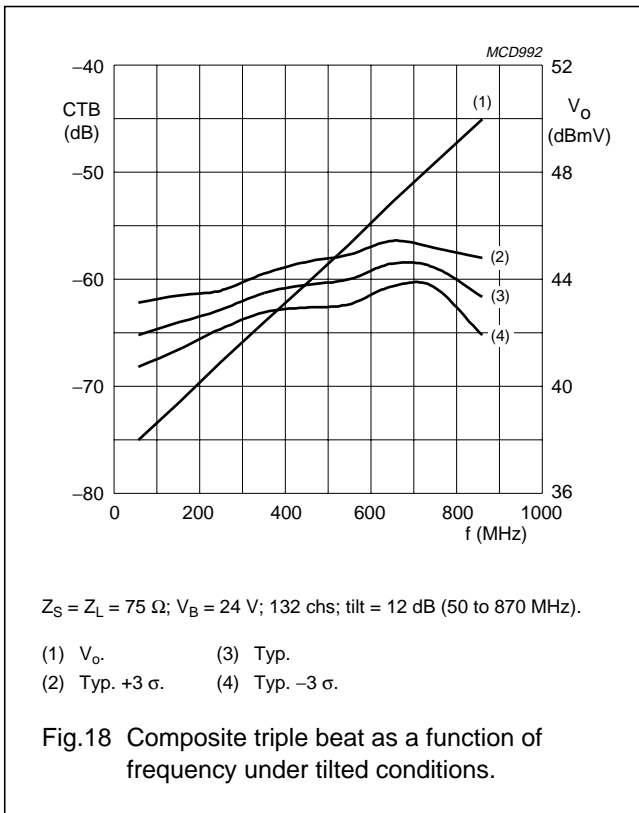
CGD914; CGD914MI





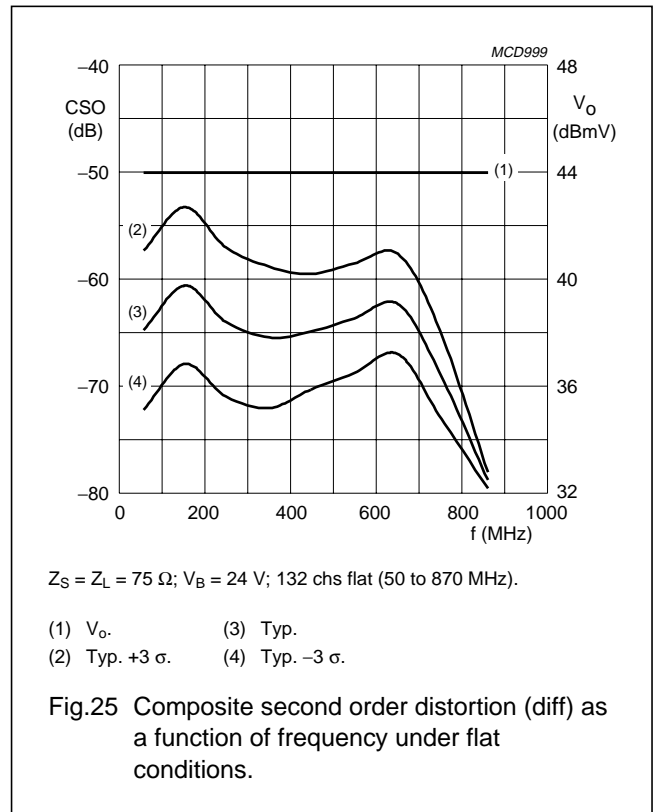
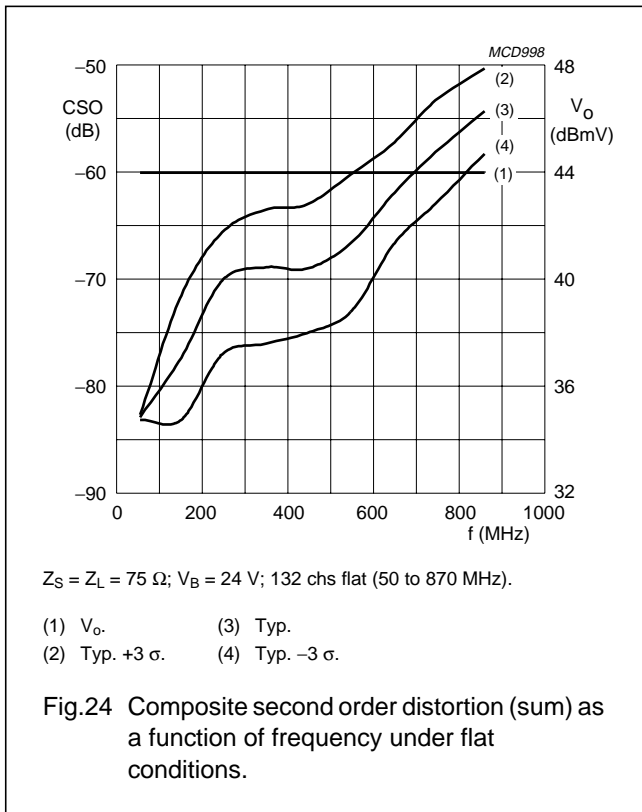
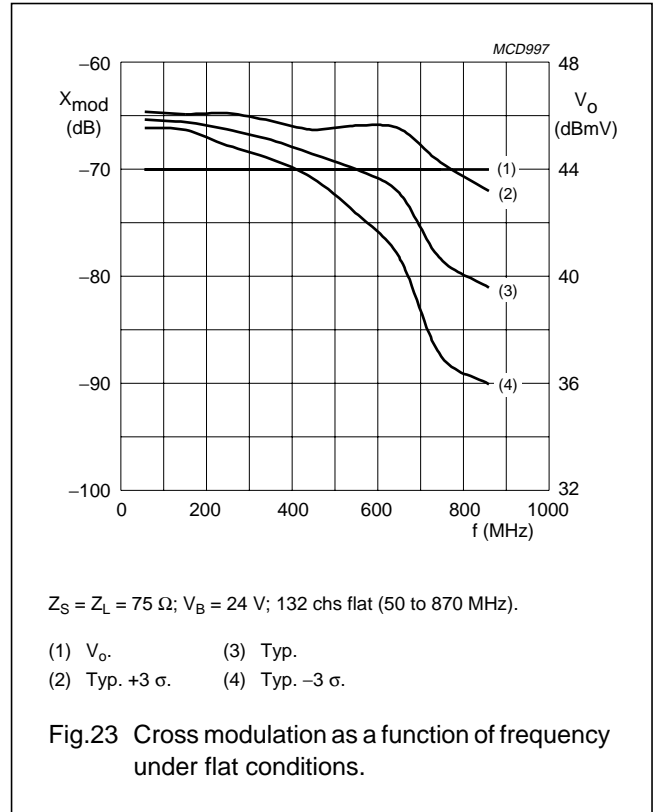
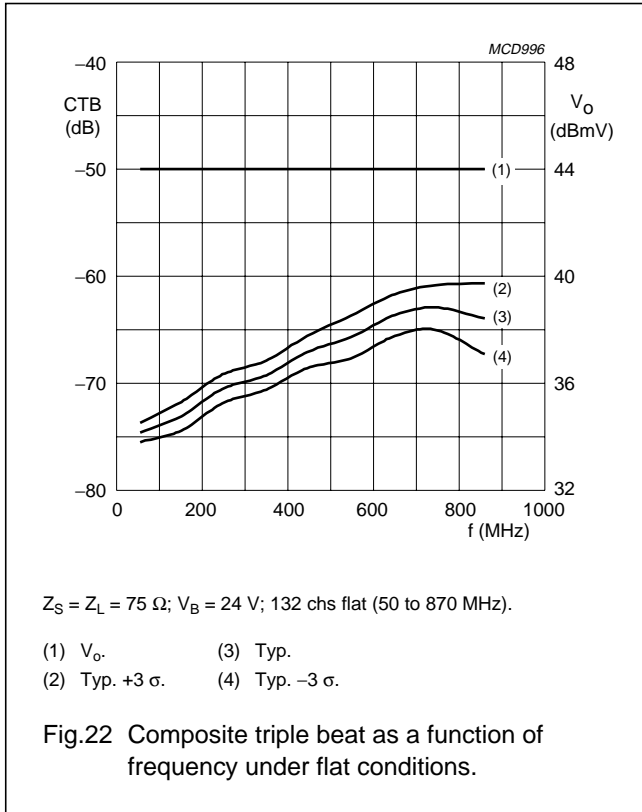
860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI



860 MHz, 20 dB gain power doubler amplifier

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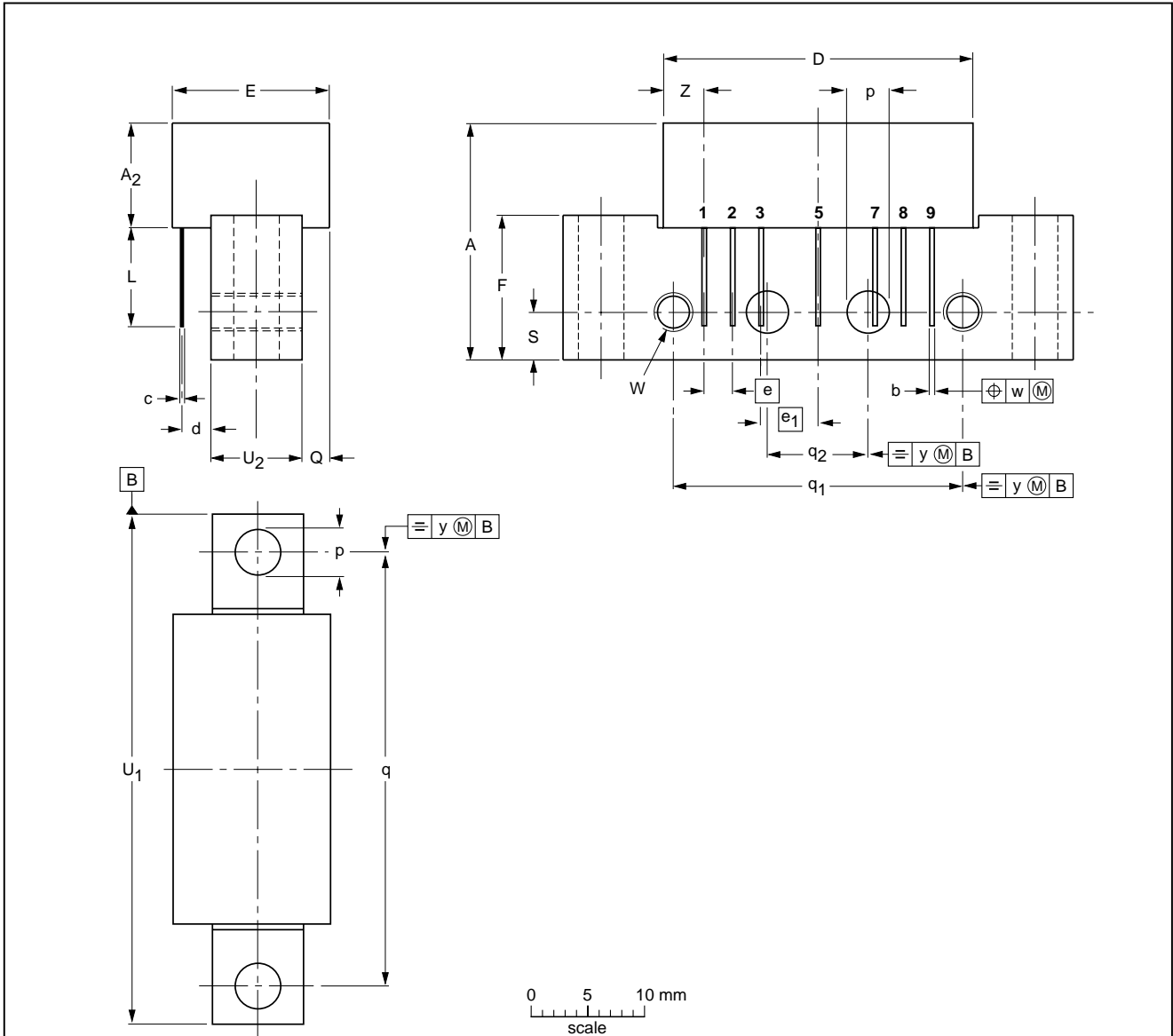
860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>2</sub> max.	b	c	D max.	d max.	E max.	e	e <sub>1</sub>	F	L min.	p	Q max.	q	q <sub>1</sub>	q <sub>2</sub>	S	U <sub>1</sub> max.	U <sub>2</sub>	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

## 860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI

## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A, and SNW-FQ-302B.

860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI

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**NOTES**

860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI

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**NOTES**

860 MHz, 20 dB gain power doubler amplifier

CGD914; CGD914MI

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**NOTES**

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